

Please type a plus sign (+) inside this box → (+)

AUG 26 2004

PTO/SB/08A (08-00)

Approved for use through 10/31/2002. OMB 0651-0031

U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449A/PTO

# **INFORMATION DISCLOSURE STATEMENT BY APPLICANT**

(use as many sheets as necessary)

## **Complete if Known**

Application Number	09/334,646
Filing Date	June 17, 1999
First Named Inventor	Shunpei YAMAZAKI et al.
Group Art Unit	2811
Examiner Name	S. Hu
Attorney Docket Number	0756-1984

Sheet 1 of 2

## **U.S. PATENT DOCUMENTS**

Examiner Initials	Cite No. <sup>1</sup>	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code <sup>2</sup> (if known)			
SP		4,330,363		Biegesen et al.	05/18/1982	
		4,466,179		Kasten	08/21/1984	
		4,784,723		Sakurai	11/15/1988	
		4,797,629		Widlar	01/10/1989	
		5,145,808		Sameshima et al.	09/08/1992	
		5,166,671		Maekawa	11/24/1992	
		5,194,853		Asada	03/16/1993	
		5,247,375		Mochizuki et al.	09/21/1993	
		5,250,852		Ovens et al.	10/05/1993	
		5,256,916		Thurston	10/26/1993	
		5,264,383		Young	11/23/1993	
		5,335,023		Edwards	08/02/1994	
		5,357,290		Horibe	10/18/1994	
		5,365,875		Asai et al.	11/22/1994	
		5,372,836		Imahashi et al.	12/13/1994	
		5,403,762		Takemura	04/04/1995	
		5,413,958		Imahashi et al.	05/09/1995	
		5,432,122		Chae	07/11/1995	
		5,432,527		Yanai et al.	07/11/1995	
		5,471,225		Parks	11/28/1995	
		5,477,073		Wakai et al.	12/19/1995	
		5,589,406		Kato et al.	12/31/1996	
		5,594,569		Konuma et al.	01/14/1997	
		5,597,740		Ito et al.	01/28/1997	
		5,643,826		Ohtani et al.	07/01/1997	
		5,648,277		Zhang et al.	07/15/1997	
		5,680,149		Koyama et al.	10/21/1997	
		5,764,206		Koyama et al.	06/09/1998	
		5,798,742		Watatani et al.	08/25/1998	
		5,923,962		Ohtani et al.	07/13/1999	
		6,549,184		Koyama et al.	04/15/2003	
		2001/0045931		Koyama et al.	11/29/2001	

## **FOREIGN PATENT DOCUMENTS**

Examiner Initials	Cite No. <sup>1</sup>	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>3</sup>
		Office <sup>3</sup>	Number <sup>4</sup>	Kind Code <sup>2</sup> (if known)				
SP		EP	0 657 863			06/14/1995		Eng.
SP		JP	58-127318			07/29/1983		Abst.
SP		JP	59-161014			09/11/1984		Abst.
Examiner Signature	Shunpei Yamazaki					Date Considered	11/09/04	

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Please type a plus sign (+) inside this box → [ + ]

PTO/SB/08A (08-00)

Approved for use through 10/31/2002. OMB 0651-0031

U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1996, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form PTO <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> (use as many sheets as necessary)				<b>Complete if Known</b>		
				Application Number	09/334,646	
Sheet		2	of	2	Filing Date	June 17, 1999
					First Named Inventor	Shunpei YAMAZAKI et al.
					Group Art Unit	2811
					Examiner Name	S. Hu
					Attorney Docket Number	0756-1984

U.S. PATENT DOCUMENTS						
Examiner Initials	Cite No. <sup>1</sup>	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code <sup>2</sup> (if known)			

FOREIGN PATENT DOCUMENTS								
Examiner Initials	Cite No. <sup>1</sup>	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>4</sup>
		Office <sup>3</sup>	Number <sup>4</sup>	Kind Code <sup>5</sup> (if known)				
SR		JP	04-282869			10/07/1992		Abst.
		JP	05-001893			01/08/1993		Abst.
		JP	05-175235			07/13/1993		Full
		JP	05-203977			08/13/1993		Full

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
SR		I. Fujieda et al., <i>Self-Referenced Poly-Si TFT Amplifier Readout for a Linear Image Sensor</i> , IEDM '93, Proc., 1993, Pages 587-590.	
		M. Bonnel et al., <i>Polycrystalline Silicon Thin-Film Transistors with Two-Step Annealing Process</i> , IEEE Electron Device Letters, Vol. 14, No. 12, December 1993, Pages 551-553.	
		M. Fuse et al., <i>Performance of Poly-Si Thin Film Transistors Fabricated by Excimer-Laser Annealing of SiH<sub>4</sub>- and Si<sub>2</sub>H<sub>6</sub>- Source Low Pressure Vapor Deposited a-Si Films With or Without Solid-Phase Crystallization</i> , Solid State Phenomena, Vols. 37-38, 1994, Pages 565-570.	

Examiner Signature	<i>Shounpei Yamazaki</i>	Date Considered	11/09/04
-----------------------	--------------------------	--------------------	----------

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<sup>1</sup> Unique citation designation number. <sup>2</sup> See attached Kinds of U.S. Patent Documents. <sup>3</sup> Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). <sup>4</sup> For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. <sup>5</sup> Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. <sup>6</sup> Applicant is to place a check mark here if English language Translation is attached.

<sup>1</sup> Unique citation designation number. <sup>2</sup> Applicant is to place a check mark here if English language Translation is attached.

Burden Hour Statement: This form is estimated to take 2.0 hours to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

Please type a plus sign (+) inside this box → [+]

PTO/SB/08A (08-00)

Approved for use through 10/31/2002. OMB 0651-0031

U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449A/PTO		<b>Complete if Known</b>	
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> APR 09 2004 (Use as many sheets as necessary)		Application Number	09/334,646
		Filing Date	June 17, 1999
		First Named Inventor	Shunpei YAMAZAKI et al.
		Group Art Unit	2811
		Examiner Name	Shouxiang Hu
		Attorney Docket Number	0756-1984
Sheet 1	of 1		

U.S. PATENT DOCUMENTS						
Examiner Initials <sup>1</sup>	Cite No. <sup>1</sup>	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code <sup>2</sup> (if known)			
SP SH		4,877,980		Kubinec	10/31/1989	
		4,999,529		Morgan, Jr. et al.	03/12/1991	

FOREIGN PATENT DOCUMENTS								
Examiner Initials <sup>1</sup>	Cite No. <sup>1</sup>	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>6</sup>
		Office <sup>3</sup>	Number <sup>4</sup>	Kind Code <sup>3</sup> (if known)				
SP SH		JP	05-323375			12/07/1993		AB

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials <sup>1</sup>	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>3</sup>

Examiner Signature	<i>Shouxiang Hu</i>	Date Considered	11/09/04
--------------------	---------------------	-----------------	----------

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<sup>1</sup> Unique citation designation number. <sup>2</sup> See attached Kinds of U.S. Patent Documents. <sup>3</sup> Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). <sup>4</sup> For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. <sup>5</sup> Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. <sup>6</sup> Applicant is to place a check mark here if English language Translation is attached.

<sup>1</sup> Unique citation designation number. <sup>2</sup> Applicant is to place a check mark here if English language Translation is attached.

Burden Hour Statement: This form is estimated to take 2.0 hours to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, Washington, DC 20231. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, Washington, DC 20231.



Sheet 1 of 1

Form PTO-1449  
(Rev. 8-83)U.S. Department of Commerce  
Patent and Trademark Office

Attorney Docket No. 0756-1984

Serial No. Not Yet Assigned

## INFORMATION DISCLOSURE STATEMENT

(Use several sheets if necessary)

Applicant: Shunpei YAMAZAKI et al.

Filing Date: June 17, 1999

Group: 2811

## U.S. PATENT DOCUMENTS

Examiner Initial	Patent Number	Date	Name	Class	Subclass	Filing Date (if appropriate)
	5,581,092	12/03/96	Takemura			
	5,500,538	03/19/96	Yamazaki et al.			
	5,147,826	09/15/92	Liu et al.			
	5,275,851	01/04/94	Fonash et al.			
	5,731,613	03/24/98	Yamazaki	257	350	
	5,581,092	12/03/96	Takemura	257	192	

## FOREIGN PATENT DOCUMENTS

Document Number	Date	Country	Class	Subclass	Translation
					Yes No

## OTHER DOCUMENTS (Including Author, Title, Relevant Pages, Date, Place of Publication)

Sfe	C. Hayzelden et al., "In Situ Transmission Electron Microscopy Studies of Silicide-Mediated Crystallization of Amorphous Silicon" (3 pages)
Sfe	A.V. Dvurechenskii et al., "Transport Phenomena in Amorphous Silicon Doped by Ion Implantation of 3d Metals", <u>Akademikian Lavrentev Prospekt 13</u> , 630090 Novosibirsk 90, USSR, pp. 635-640.
	T. Hempel et al., "Needle-Like Crystallization of Ni Doped Amorphous Silicon Thin Films", <u>Solid State Communications</u> , Vol. 85, No. 11, pp. 921-924, 1993.
	R. Kakkad et al., "Crystallized Si films by low-temperature rapid thermal annealing of amorphous silicon," <u>J. Appl. Phys.</u> , 65(5), March 1, 1989, pp. 2069-72.
	G. Liu et al., "Polycrystalline silicon thin film transistors on Corning 7059 glass substrates using short time, low-temperature processing," <u>Appl. Phys. Lett.</u> 62(20), May 17, 1993, pp. 2554-2556.
	G. Liu et al., "Selective area crystallization of amorphous silicon films by low-temperature rapid thermal annealing," <u>Appl. Phys. Lett.</u> 55(7), August 14, 1989, pp. 660-662.
Sfe	R. Kakkad et al., "Low Temperature Selectiv Crystallization of Amorphous Silicon," <u>Journal of Non-Crystalline Solids</u> , 115, 1989, pp. 66-68.

Examiner

*Shounpei Yamazaki*

Date Considered

11/09/04

\*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.